

INFORMATION DISCLOSURE STATEMENT

Applicant	: Yasuyoshi Hyodo, et al.
App. No.	: Unknown
Filed	: Herewith
For	: METHOD OF FORMING SILICON- CONTAINING INSULATION FILM HAVING LOW DIELECTRIC CONSTANT AND LOW FILM STRESS
Examiner	: Unknown
Group Art Unit	: Unknown

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Enclosed is form PTO-1449 listing references that are also enclosed.

This Information Disclosure Statement is being filed within three months of the filing date of this application or upon filing if this is a CPA or RCE, and no fee is required in accordance with 37 C.F.R. § 1.97(b)(1), (b)(2), or (b)(4).

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: August 20, 2003

By: 

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FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMPJ.137AUS	APPLICATION NO. Unknown
		APPLICANT Yasuyoshi Hyodo, et al.	
		FILING DATE Herewith	GROUP Unknown

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

**EXAMINER
INITIAL**

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

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